



JM38510/13503

LOW-NOISE PRECISION
OPERATIONAL AMPLIFIER

Precision Monolithics Inc.

T-79-06-10

FEATURES

- Low V_{OS} 25 μ V
- Low V_{OS} Drift 0.6 μ V/ $^{\circ}$ C
- High Speed 1.7V/ μ s
- Low Noise 0.18 μ V_{p-p}
- High Gain 1.0 Million
- Wide Supply Voltage Range \pm 4.5V to \pm 18V

temperature range or reliability factors equivalent to the MIL-M-38510 device.

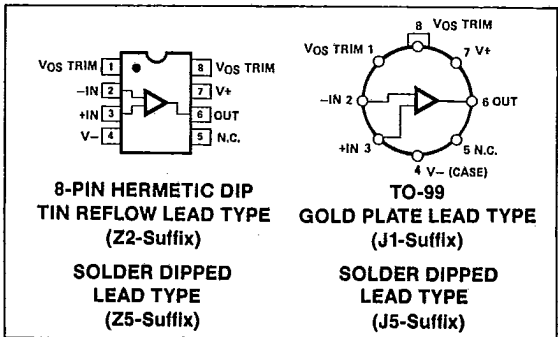
MILITARY DEVICE TYPE	GENERIC-INDUSTRY TYPE
03	OP27A

For an 833-processed device with Improved electrical specifications, review the OP-27 data sheet.

ORDERING INFORMATION

JAN SLASH SHEET	PMI DEVICE
JM38510/13503BGC	OP27AJ1/38510
JM38510/13503BGA	OP27AJ5/38510
JM38510/13503SGA	OP27SAJ5/38510
JM38510/13503BPB	OP27AZ2/38510
JM38510/13503BPA	OP27AZ5/38510
JM38510/13503SPA	OP27SAJ5/38510

PIN CONNECTIONS



GENERAL DESCRIPTION

This data sheet covers the electrical requirements for a monolithic, low offset voltage, internally-compensated operational amplifier as specified in MIL-M-38510/135 for device type 03. Devices supplied to this data sheet are manufactured and tested at PMI's MIL-M-38510 certified facility and are listed in QPL-38510.

Complete device requirements will be found in MIL-M-38510 and MIL-M-38510/135 for Class B and Class S processed devices.

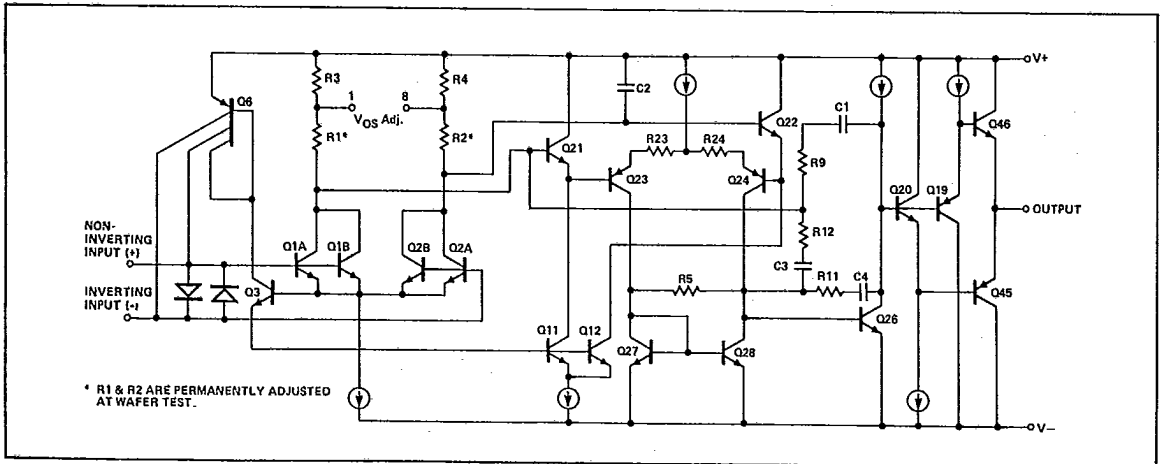
GENERIC CROSS-REFERENCE INFORMATION

This cross-reference information is presented for the convenience of the user. The generic-industry types listed may not have identical operational performance characteristics across the military

POWER AND THERMAL CHARACTERISTICS

Case Outline	Package	Maximum Allowable Power Dissipation	Maximum θ_{JC}	Maximum θ_{JA}
P	Dual-In-Line	208mW @ $T_A = 125^{\circ}$ C	50 $^{\circ}$ C/W	120 $^{\circ}$ C/W
G	8-Lead-CAN	167mW @ $T_A = 125^{\circ}$ C	40 $^{\circ}$ C/W	150 $^{\circ}$ C/W

SIMPLIFIED SCHEMATIC



5-601

8/89, Rev. A3

5 OPERATIONAL AMPLIFIERS/BUFFERS

[PMI]

JM38510/13503 LOW-NOISE PRECISION OPERATIONAL AMPLIFIER

ABSOLUTE MAXIMUM RATINGS

Supply Voltage (V_{CC})	$\pm 22V$
Input Voltage Range (V_{IN})	$\pm V_{CC}$
Differential Input Voltage Range	$\pm 0.7V$
Output Short-Circuit Duration (Note 1)	
Lead Temperature (Soldering, 60 sec)	$+300^{\circ}C$
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
Junction Temperature (T_J)	$+150^{\circ}C$
Maximum Power Dissipation (P_D) (Note 2)	500mW

RECOMMENDED OPERATING CONDITIONS

Supply Voltage Range	$\pm 4.5V$ to $\pm 18V$
Ambient Temperature Range	$-55^{\circ}C$ to $+125^{\circ}C$

T-79-06-10

NOTES:

- Output may be shorted to ground indefinitely at $V_S = \pm 15V$, $T_A = 25^{\circ}C$. Temperature and/or supply voltages must be limited to ensure dissipation rating is not exceeded.
- Maximum power dissipation versus ambient temperature.

ELECTRICAL CHARACTERISTICS at $\pm 4.5V \leq V_{CC} \leq \pm 20V$ and $-55^{\circ}C \leq T_A \leq 125^{\circ}C$, $R_S = 50\Omega$ unnullified, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	03 LIMITS		UNITS
			MIN	MAX	
Input Offset Voltage	V_{IO}	$T_A = 25^{\circ}C$ (Notes 1, 2)	-25 -60	25 60	μV
Input Offset Voltage Temperature Sensitivity	$\Delta V_{IO}/\Delta T$	(Note 1)	-0.6	0.6	$\mu V/^{\circ}C$
Input Bias Current	$+I_{IB}$	$T_A = 25^{\circ}C$ (Note 1)	-40 -60	40 60	nA
	$-I_{IB}$	$T_A = 25^{\circ}C$ (Note 1)	-40 -60	40 60	
Input Offset Current	I_{IO}	$T_A = 25^{\circ}C$ (Note 1)	-35 -50	35 50	nA
	+PSRR	$+V_{CC} = 18V$ to $5V$, $-V_{CC} = -15V$ $T_A = 25^{\circ}C$	—	10	
Power Supply Rejection Ratio	-PSRR	$+V_{CC} = 15V$, $-V_{CC} = -18V$ to $-5V$ $T_A = 25^{\circ}C$	—	10	$\mu V/V$
	+PSRR	$+V_{CC} = 18V$ to $5V$, $-V_{CC} = -15V$	—	16	
	-PSRR	$+V_{CC} = 15V$, $-V_{CC} = -18V$ to $-5V$	—	16	
	PSRR	$V_{CC} = \pm 4.5V$ to $\pm 18V$ $T_A = 25^{\circ}C$	—	10	
		$V_{CC} = \pm 4.5V$ to $\pm 18V$	—	16	

NOTES:

- Tested at $V_{CM} = 0$, $V_{CC} = \pm 15V$.
- Due to the inherent warm-up drift, testing shall occur no sooner than three (3) minutes after application of power.



ELECTRICAL CHARACTERISTICS at $\pm 4.5V \leq V_{CC} \leq \pm 20V$ and $-55^\circ C \leq T_A \leq +125^\circ C$, $R_S = 50\Omega$ unnullled, unless otherwise noted. *Continued*

T-79-06-10

PARAMETER	SYMBOL	CONDITIONS	03 LIMITS		UNITS
			MIN	MAX	
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 11V, T_A = +25^\circ C, V_{CC} = \pm 15V$	114	—	dB
		$V_{CM} = \pm 10V, V_{CC} = \pm 15V$	108	—	
Adjustment for Input Offset	$V_{IO} \text{ Adj (+)}$	$T_A = +25^\circ C, \text{ (Note 1)}$	0.5	—	mV
	$V_{IO} \text{ Adj (-)}$	$T_A = +25^\circ C, \text{ (Note 1)}$	—	-0.5	
Output Short-Circuit Current	$i_{OS(+)}$ $i_{OS(-)}$	$t \leq 25\text{ms}, \text{ (Notes 1,3)}$	-70	—	mA
		$t \leq 25\text{ms}, \text{ (Notes 1,3)}$	—	70	
Supply Current	I_{CC}	$T_A = +25^\circ C \text{ (Note 1)}$	—	5	mA
			—	6	
Output Voltage Swing (Minimum)	V_{OP}	$R_L = 600\Omega, \text{ (Note 1)}$	-10	10	V
		$R_L = 2k\Omega, \text{ (Note 1)}$	-11.5	11.5	
Open Loop Voltage Gain (Single Ended)	A_{VS}	$T_A = +25^\circ C \text{ (Note 2)}$	1000	—	V/mV
			600	—	
Slew Rate	SR(+), SR(-)	$V_{IN} = 10V, T_A = +25^\circ C, \text{ (Note 1)}$	1.7	—	V/ μ s
Input Noise Voltage Density	e_n	$f_O = 10\text{Hz}$ $f_O = 100\text{Hz}$ $f_O = 1\text{kHz}$ $T_A = +25^\circ C, \text{ (Note 1)}$	—	5.5	nV/ $\sqrt{\text{Hz}}$
			—	4.0	
			—	3.8	
Low Frequency Input Noise Voltage	e_{np-p}	$f = 0.1\text{Hz to } 10\text{Hz}$ $T_A = +25^\circ C, \text{ (Note 1)}$	—	0.18	μ V _{p-p}
Input Noise Current Density	i_n	$f_O = 10\text{Hz}$ $f_O = 100\text{Hz}$ $f_O = 1\text{kHz}$ $T_A = +25^\circ C, \text{ (Note 1)}$	—	5.66	pA/ $\sqrt{\text{Hz}}$
			—	1.88	
			—	0.84	

NOTES:

1. Tested at $V_{CM} = 0, V_{CC} = \pm 15V$.
2. $V_{OUT} = 0$ to $+10$ for $A_{VS}(+)$ and $V_{OUT} = 0$ to $-10V$ for $A_{VS}(-)$. $R_L = 2,000\Omega$.
3. Continuous short-circuit limits are considerably less than the indicated test limits, since maximum power dissipation cannot be exceeded.


 OPERATIONAL AMPLIFIERS/BUFFERS